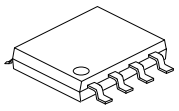
-35A, -60V P-CHANNEL POWER MOSFET



SOP-8

■ DESCRIPTION

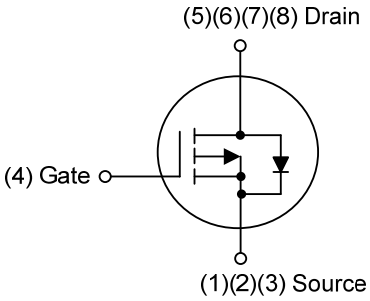
The UTC **UT35P06** is P-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with ideal for low voltage inverter applications.

The UTC **UT35P06** is suitable for high efficiency synchronous rectification in SMPS, UPS, hard switched and high frequency circuits.

■ FEATURES

* $R_{DS(ON)}$ ≤ 30 mΩ @ V_{GS}=-10V, I_D=-17.5A
  $R_{DS(ON)}$ ≤ 40 mΩ @ V_{GS}=-4.5V, I_D=-17.5A
* High Cell Density Trench Technology
* High Power and Current Handling Capability

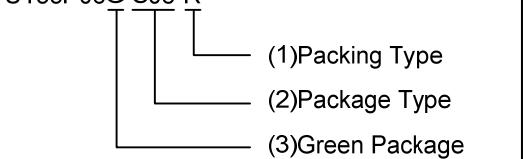
■ SYMBOL



■ ORDERING INFORMATION

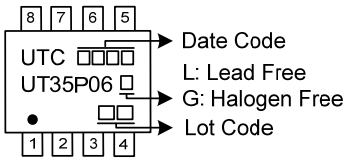
Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UT35P06L-S08-R	UT35P06G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) R: Tape Reel
(2) S08: SOP-8
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	Continuous	I_D	-35	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	-70	A
Single Pulsed Avalanche Energy (Note 3)		E_{AS}	45	mJ
Power Dissipation		P_D	2.7	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=0.1mH, I_{AS}=-30A, V_{DD}=-50V, R_G=25 Ω, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	125	°C/W
Junction to Case	θ_{JC}	45	°C/W

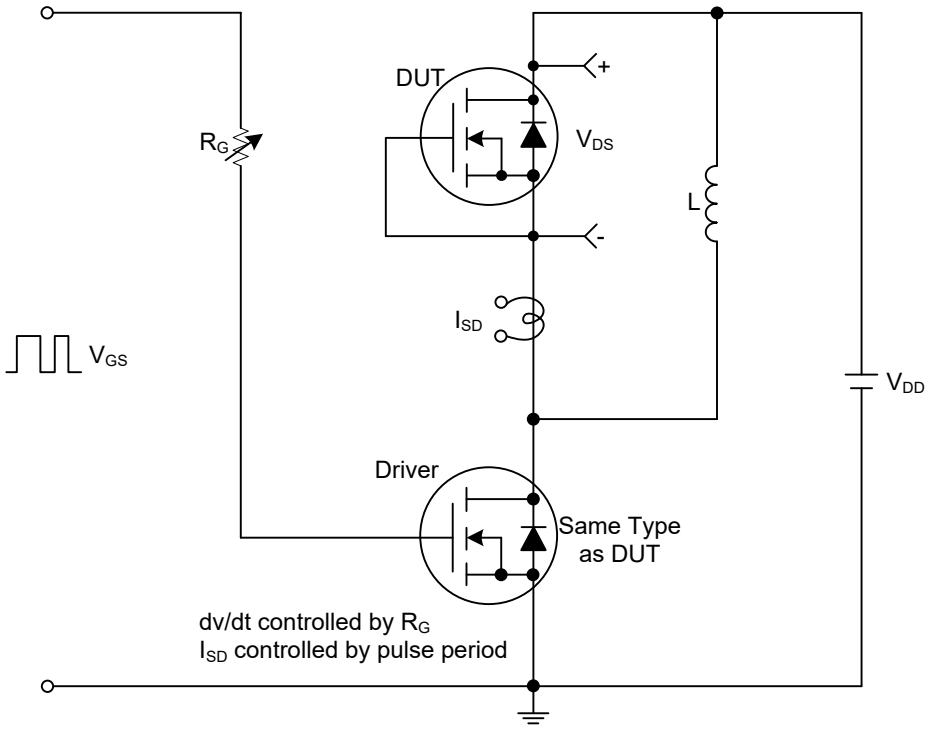
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

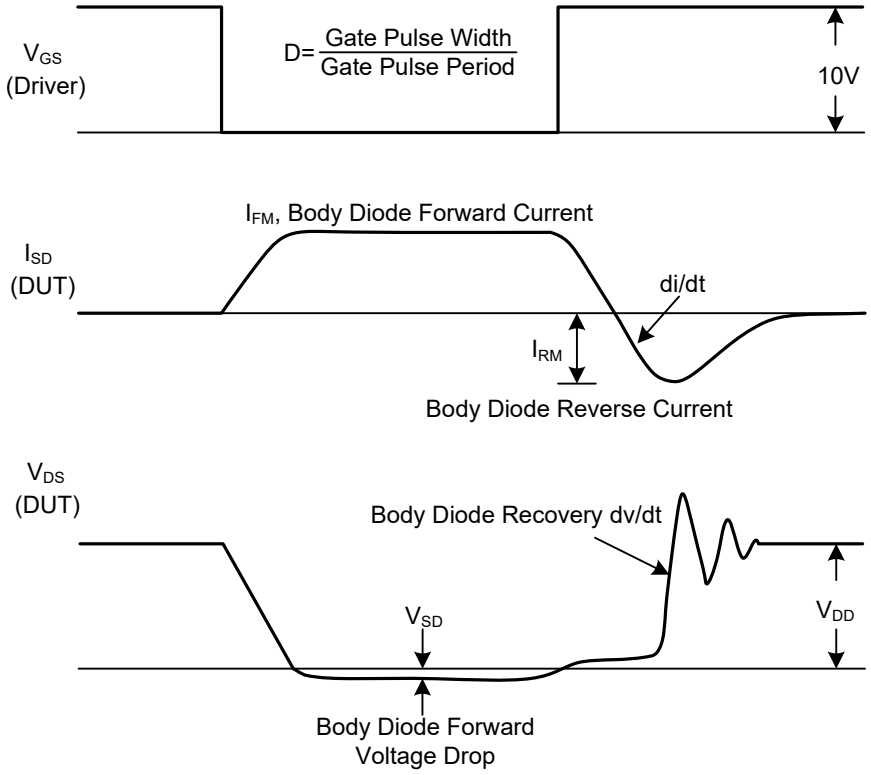
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=-250μA, V_{GS}=0V	-60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=-60V, V_{GS}=0V, T_J =25°C			-1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.0		-3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=-10V, I_D=-17.5A			30	mΩ
			V_{GS}=-4.5V, I_D=-17.5A			40	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=-25V, f=1.0MHz		2900		pF
Output Capacitance		C_{OSS}			235		pF
Reverse Transfer Capacitance		C_{RSS}			160		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=-48V, V_{GS}=-10V, I_D=-35A, (Note 1, 2)		60		nC
Gate to Source Charge		Q_{GS}			9		nC
Gate to Drain Charge		Q_{GD}			17		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=-30V, V_{GS}=-10V, I_D=-35A, R_G=3Ω (Note 1, 2)		8		ns
Rise Time		t_R			18		ns
Turn-off Delay Time		$t_{D(OFF)}$			70		ns
Fall-Time		t_F			35		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				-35	A
Maximum Body-Diode Pulsed Current		I_{SM}				-70	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S=-35A, V_{GS}=0V			-1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=-35A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		60		ns
Reverse Recovery Charge		Q_{rr}			90		ns

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



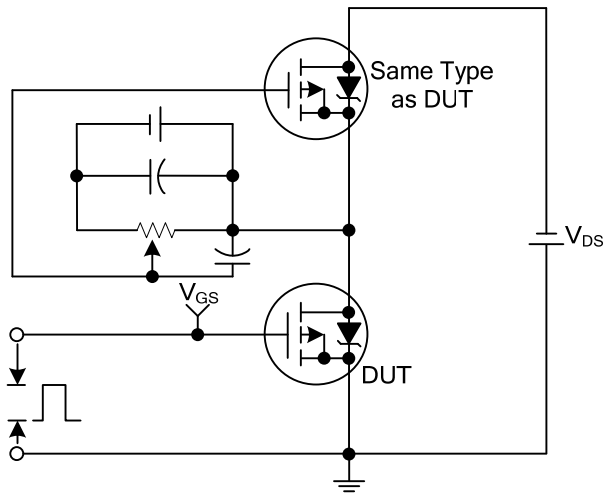
Peak Diode Recovery dv/dt Test Circuit



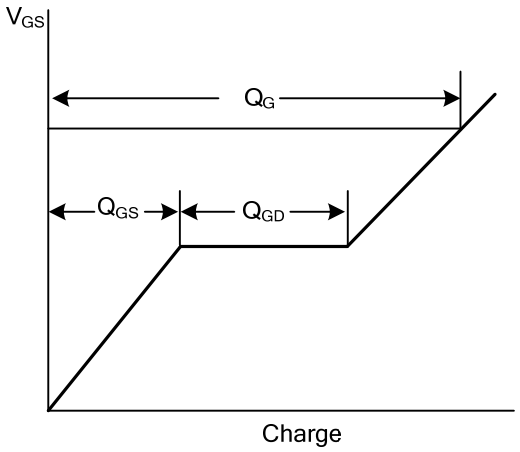
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

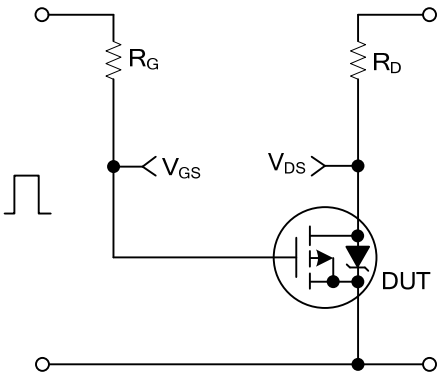
■ TEST CIRCUITS AND WAVEFORMS



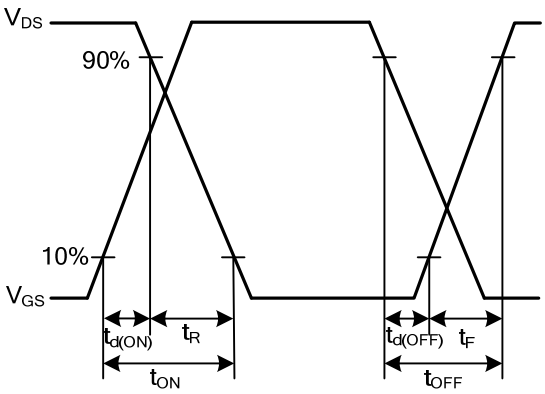
Gate Charge Test Circuit



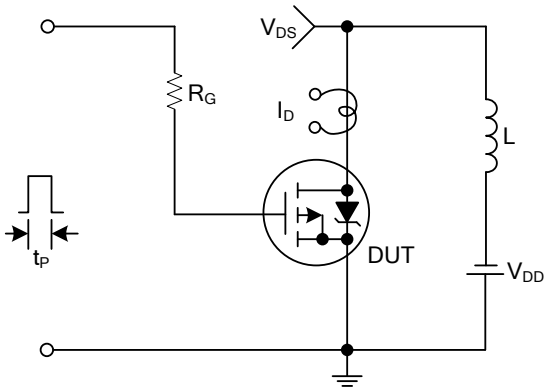
Gate Charge Waveforms



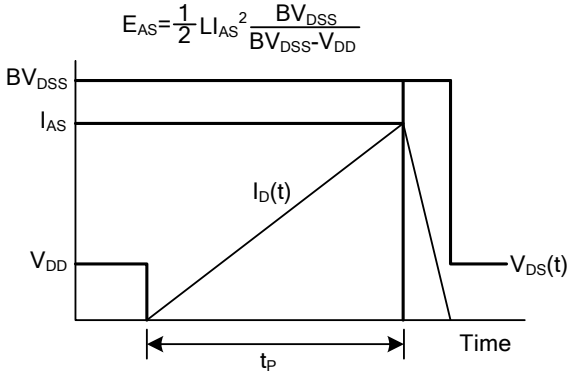
Resistive Switching Test Circuit



Resistive Switching Waveforms



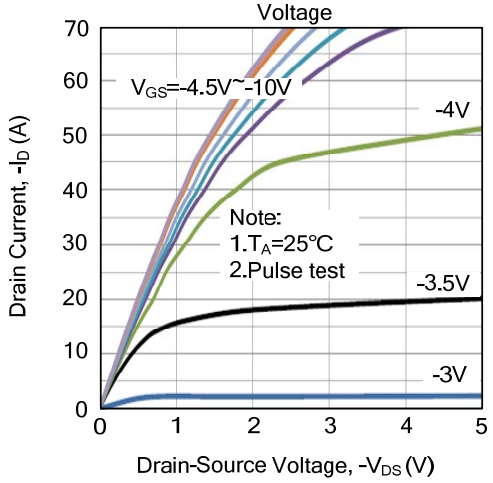
Unclamped Inductive Switching Test Circuit



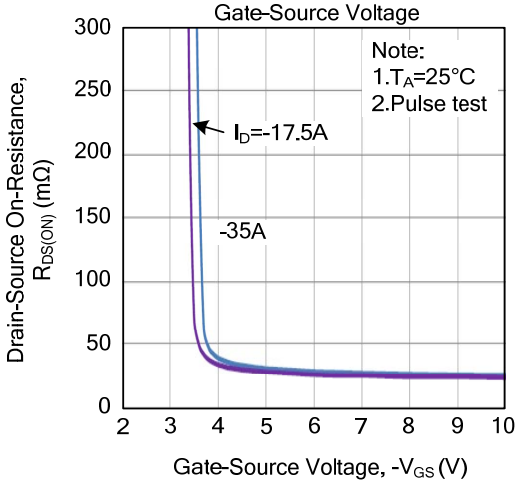
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

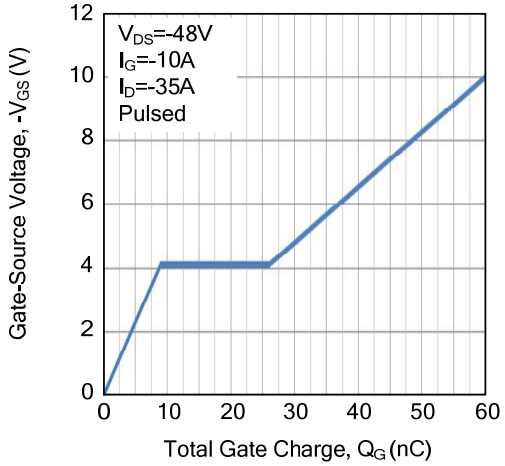
Drain Current vs. Drain-Source Voltage



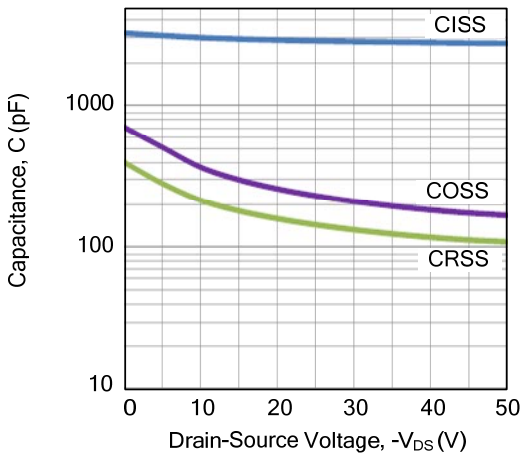
Drain-Source On-Resistance vs. Gate-Source Voltage



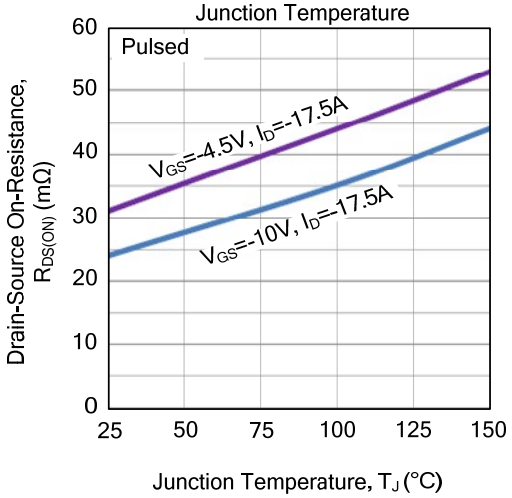
Gate Charge Characteristics



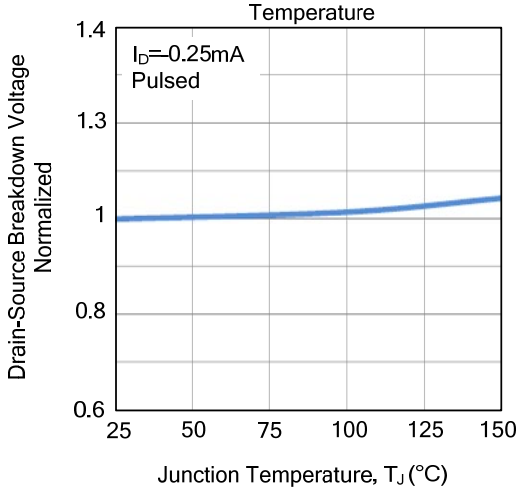
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

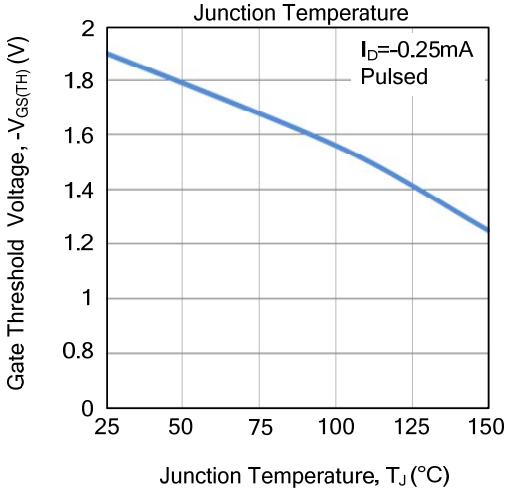


Breakdown Voltage vs. Junction Temperature

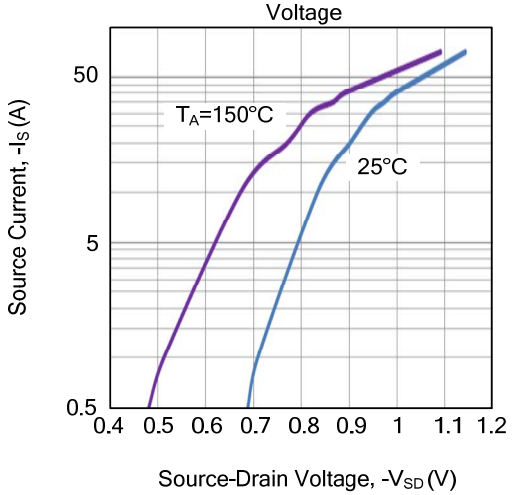


■ TYPICAL CHARACTERISTICS (Cont.)

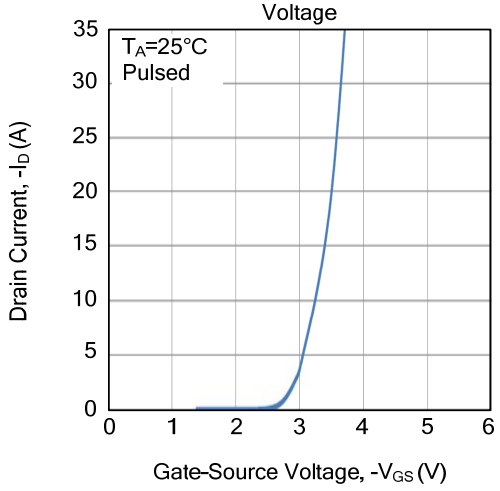
Gate Threshold Voltage vs. Junction Temperature



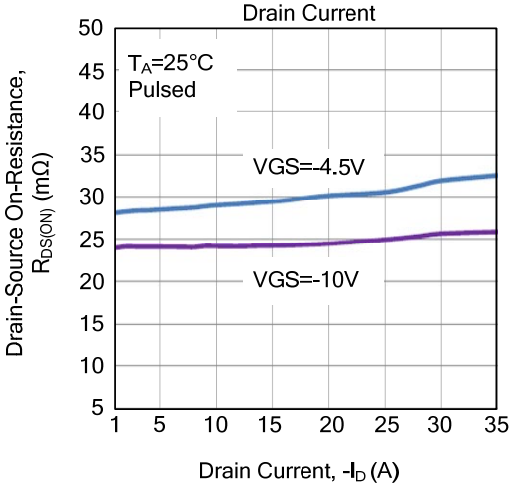
Source Current vs. Source-Drain Voltage



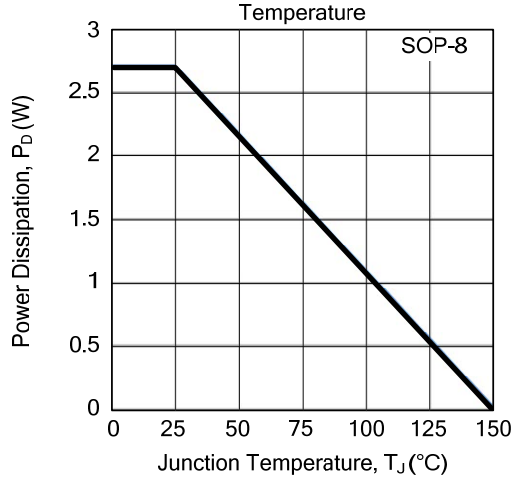
Drain Current vs. Gate-Source Voltage



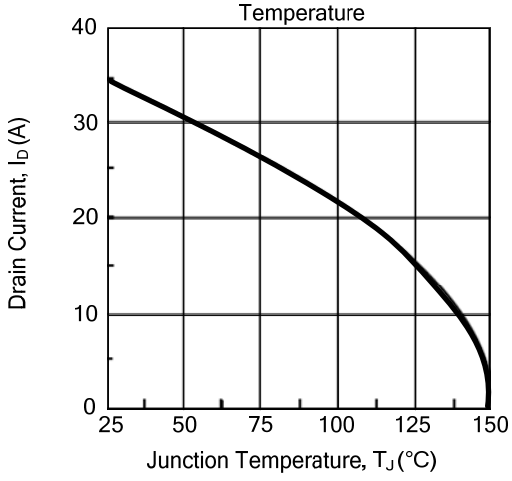
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)